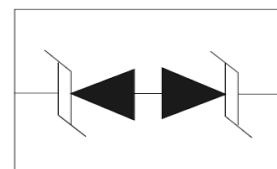


Descriptions

The ESD5451N is a bi-directional TVS (Transient Voltage Suppressor). It is specifically designed to protect sensitive electronic components which are connected to low speed data lines and control lines from over-stress caused by ESD (Electrostatic Discharge), EFT (Electrical Fast Transients) and Lightning.

The ESD5451N may be used to provide ESD protection up to $\pm 30\text{kV}$ (contact and air discharge) according to IEC61000-4-2, and withstand peak pulse current up to 8A (8/20 μs) according to IEC61000-4-5.

The ESD5451N is available in DFN1006-2L package. Standard products are Pb-free and Halogen-free.



Features

- Reverse stand-off voltage: $\pm 5\text{V}$ Max
- Transient protection for each line according to IEC61000-4-2 (ESD): $\pm 30\text{kV}$ (contact and air discharge)
IEC61000-4-4 (EFT): 40A (5/50ns)
IEC61000-4-5 (surge): 8A (8/20 μs)
- Capacitance: $C_J = 17.5\text{pF}$ typ.
- Low leakage current: $I_R < 1\text{nA}$ typ.
- Low clamping voltage: $V_{CL} = 9\text{V}$ typ. @ $I_{PP} = 16\text{A}$ (TLP)
- Solid-state silicon technology

Applications

- Cellular handsets
- Tablets
- Laptops
- Other portable devices
- Network communication devices

Absolute maximum ratings

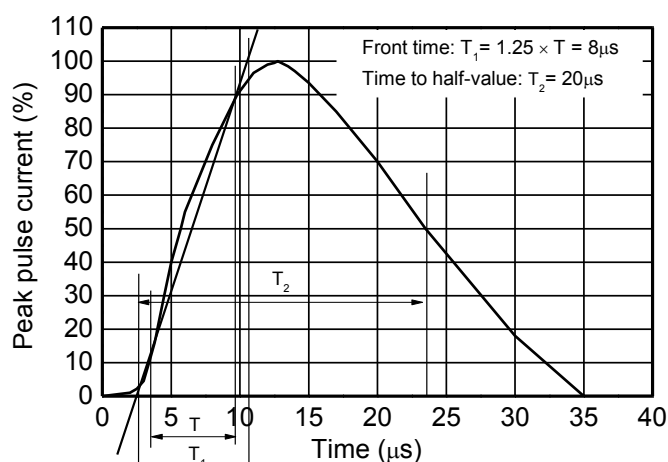
Parameter	Symbol	Rating	Unit
Peak pulse power ($t_p = 8/20\mu\text{s}$)	P_{pk}	80	W
Peak pulse current ($t_p = 8/20\mu\text{s}$)	I_{PP}	8	A
ESD according to IEC61000-4-2 air discharge	V_{ESD}	± 30	kV
ESD according to IEC61000-4-2 contact discharge		± 30	
Operation junction temperature	T_J	125	$^{\circ}\text{C}$
Lead temperature	T_L	260	$^{\circ}\text{C}$
Storage temperature	T_{STG}	-55~150	$^{\circ}\text{C}$

Electrical characteristics (T_A=25°C, unless otherwise noted)

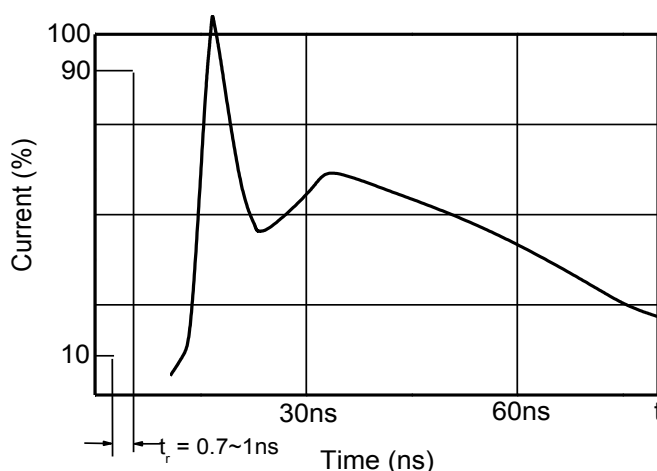
Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse stand-off voltage	V _{RWM}				±5	V
Reverse leakage current	I _R	V _{RWM} = 5V		<1	100	nA
Reverse breakdown voltage	V _{BR}	I _{BR} = 1mA	5.1			V
Reverse holding voltage	V _{HOLD}	I _{HOLD} = 50mA	5.1			V
Clamping voltage ¹⁾	V _{CL}	I _{PP} = 16A, t _p = 100ns		9		V
Clamping voltage ²⁾	V _{CL}	V _{ESD} = 8kV		9		V
Clamping voltage ³⁾	V _{CL}	I _{PP} = 1A, t _p = 8/20μs			6.5	V
		I _{PP} = 5A, t _p = 8/20μs			8.5	V
		I _{PP} = 8A, t _p = 8/20μs			10	V
Dynamic resistance ¹⁾	R _{DYN}			0.20		Ω
Junction capacitance	C _J	V _R = 0V, f = 1MHz		17.5	22	pF
		V _R = 5V, f = 1MHz		11.5	16	pF

- 1) TLP parameter: Z₀ = 50Ω , t_p = 100ns, t_r = 2ns, averaging window from 60ns to 80ns. R_{DYN} is calculated from 4A to 16A.
- 2) Contact discharge mode, according to IEC61000-4-2.
- 3) Non-repetitive current pulse, according to IEC61000-4-5.

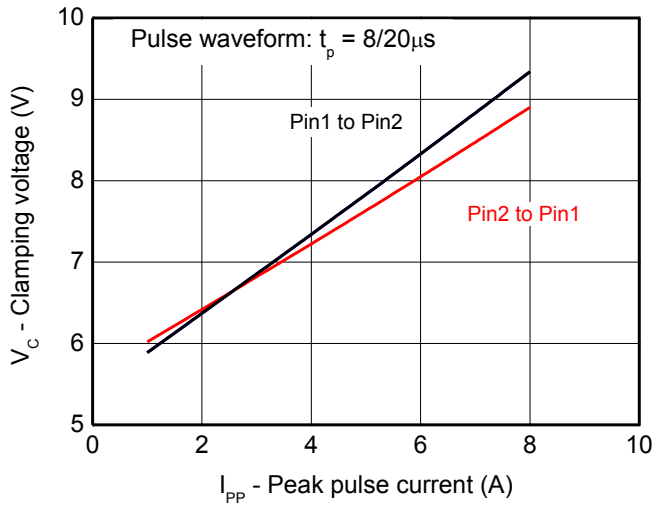
Typical characteristics (T_A=25°C, unless otherwise noted)



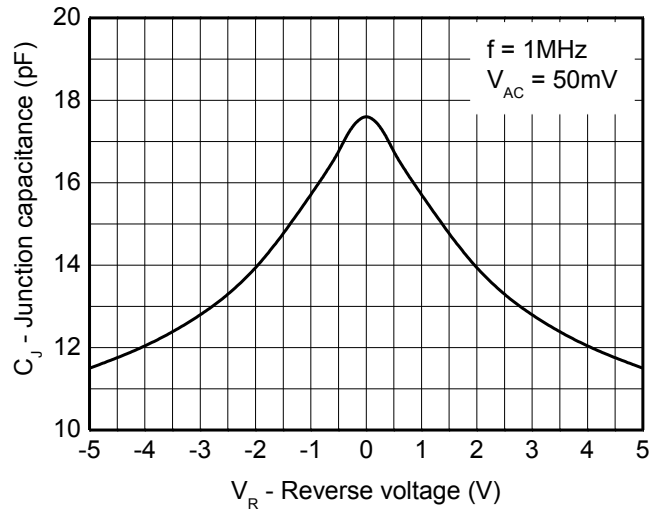
8/20μs waveform per IEC61000-4-5



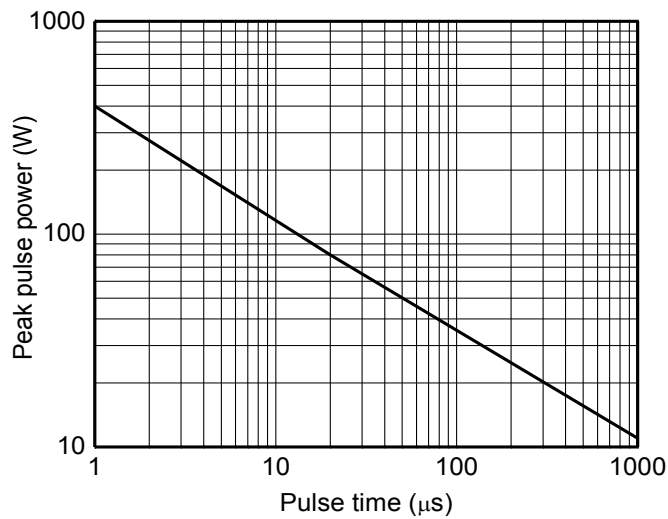
Contact discharge current waveform per IEC61000-4-2



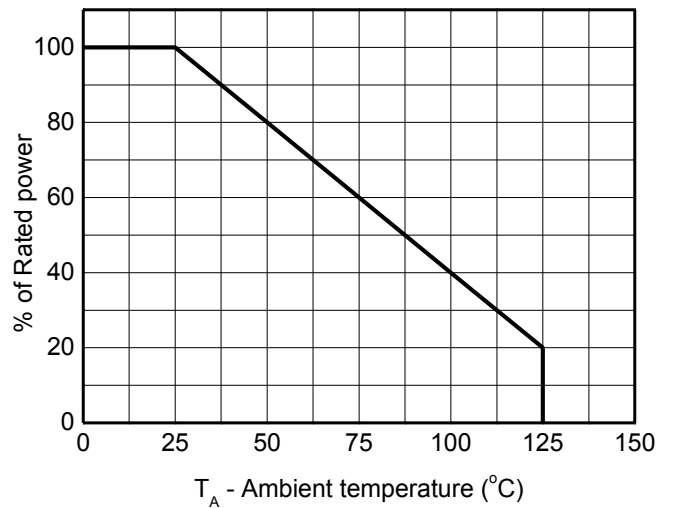
Clamping voltage vs. Peak pulse current



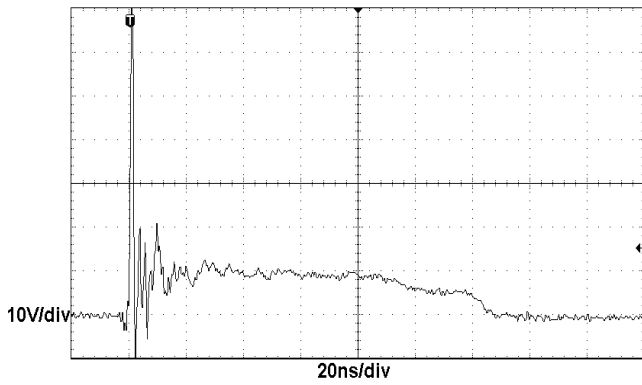
Capacitance vs. Reverse voltage



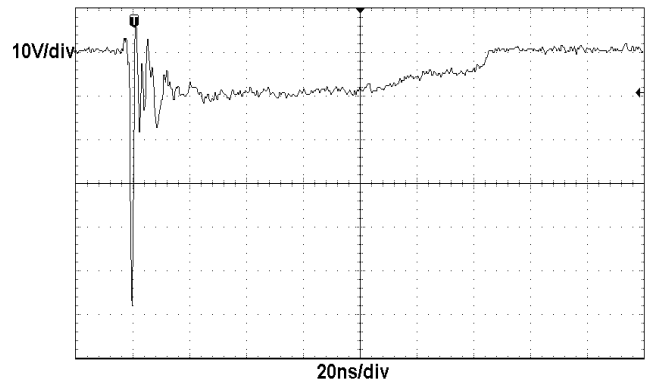
Non-repetitive peak pulse power vs. Pulse time



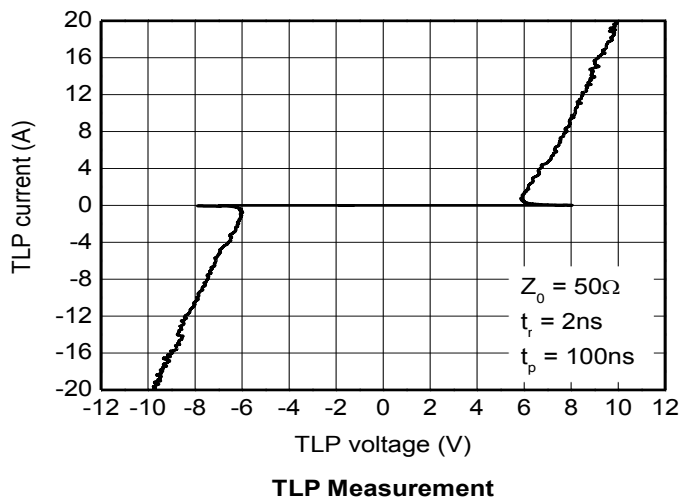
Power derating vs. Ambient temperature



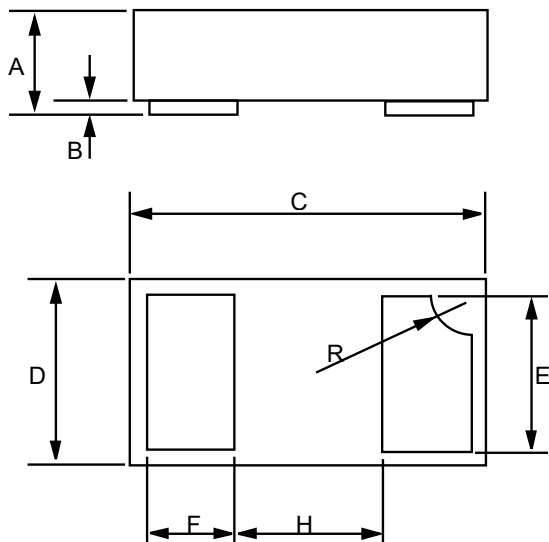
ESD clamping
 (+8kV contact discharge per IEC61000-4-2)



ESD clamping
 (-8kV contact discharge per IEC61000-4-2)

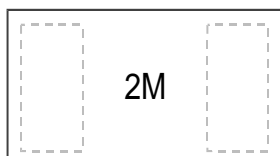


DFN1006-2 PACKAGE OUTLINE DIMENSIONS



Dim	Inches		Millimeters	
	MIN	MAX	MIN	MAX
A	0.013	0.020	0.34	0.50
B	0.000	0.002	0.00	0.05
C	0.037	0.042	0.95	1.075
D	0.021	0.026	0.55	0.675
E	0.017	0.021	0.45	0.55
F	0.007	0.011	0.20	0.30
H	0.015Typ.		0.40Typ.	
R	0.001	0.005	0.05	0.15

Marking



Ordering information

Order code	Package	Baseqty	Deliverymode
UMW ESD5451N	DFN1006-2	10000	Tape and reel